**Product data sheet** 

## 1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO247 plastic package, designed for high frequency switched-mode power supplies.



#### 2. Features and benefits

- Highly stable switching performance
- High forward surge capability I<sub>FSM</sub>
- · Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability (T<sub>i(max)</sub> = 175 °C)

## 3. Applications

- · Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values Values		Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage				1200		V
$I_{O(AV)}$	limiting average forward current	$\delta$ = 0.5; square-wave pulse; $T_{mb} \le 138$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3		20		А	
T <sub>j</sub>	junction temperature			-55 to 175		°C	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.42	1.60	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.90	2.30	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>		-	2.00	2.50	V
Dynamic	characteristics			1	1		
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_i = 25 \text{ °C}$ ; per diode; Fig. 7		-	22	-	nC

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		A1
3	A2	anode		K
mb	mb	mounting base; connected to cathode		sym125

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D201200CW	TO247	WNSC2D201200CW6Q	Tube	30	SOT429	25-Mar-2013

## 7. Marking

### Table 4. Marking codes

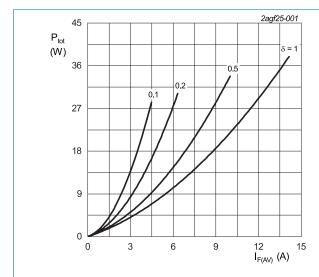
Type number	Marking codes
WNSC2D201200CW	WNSC2D 201200CW

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			1200	V
$V_{RWM}$	crest working reverse voltage			1200	V
$V_R$	reverse voltage	DC		1200	V
$I_{O(AV)}$	limiting average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 138$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3		20	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 141 °C$ ; square-wave pulse; per diode		20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		80	А
		$t_p$ = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode		750	A
l²t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 10  \text{ms}$		32	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature			-55 to 175	°C
T <sub>j</sub>	junction temperature			-55 to 175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   $V_o = 0.997 \text{ V; } R_s = 0.1192 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

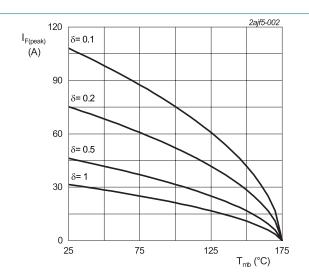
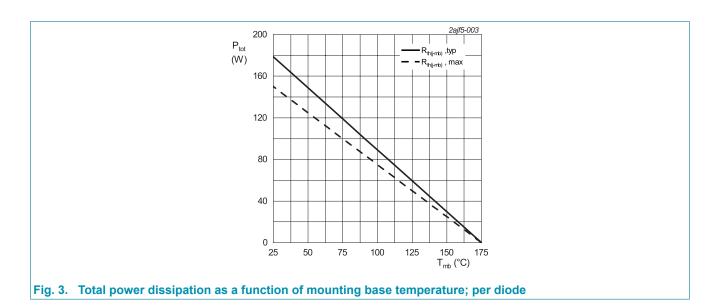


Fig. 2. Current derating as a function of mounting base temperature; per diode



### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	per diode; Fig. 4		-	0.84	1	K/W
	from junction to mounting base	both diodes conducting		-	0.45	0.55	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

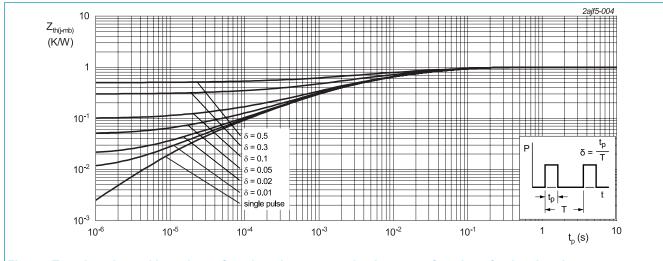
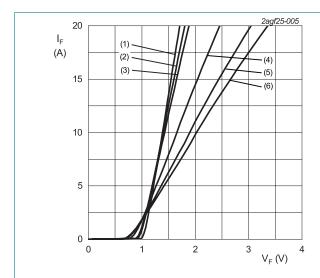


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit	
Static cha	Static characteristics							
V <sub>F</sub>	forward current	$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 5$		-	1.42	1.60	V	
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.90	2.30	V	
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>		-	2.00	2.50	V	
I <sub>R</sub>	reverse current	$V_R = 1200 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	1	50	μA	
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>		-	25	500	μA	
Dynamic	characteristics							
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \text{ per diode}; Fig. 7$		-	22	-	nC	
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C		-	481	-	pF	
		f = 1 MHz; V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C		-	42	-	pF	
		f = 1 MHz; V <sub>R</sub> = 800 V; T <sub>j</sub> = 25 °C		-	31	-	pF	
E <sub>as</sub>	non-repetitive avalanche energy	$I_R$ = 4.2 A; L = 10 mH; $T_{j(init)}$ = 25 °C; per diode		88	-	-	mJ	



 $V_0 = 0.997 \text{ V}; R_s = 0.1192 \Omega$ 

(1) T<sub>i</sub> = -55 °C; typical values

(2) T<sub>i</sub> = 0 °C; typical values

(3)  $T_j = 25$  °C; typical values (4) T<sub>j</sub> = 100 °C; typical values

(5)  $T_j = 150$  °C; typical values (6) T<sub>i</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

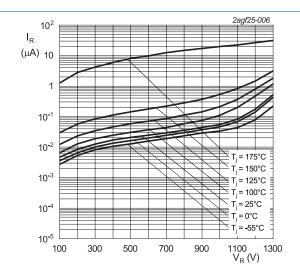


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

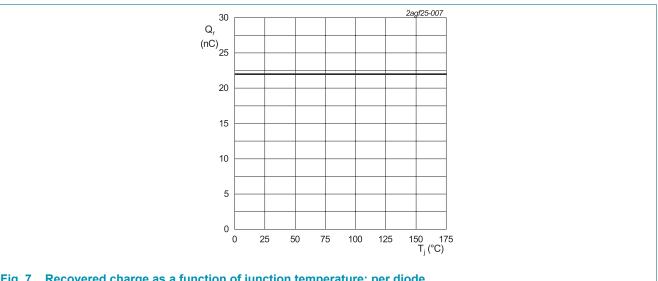
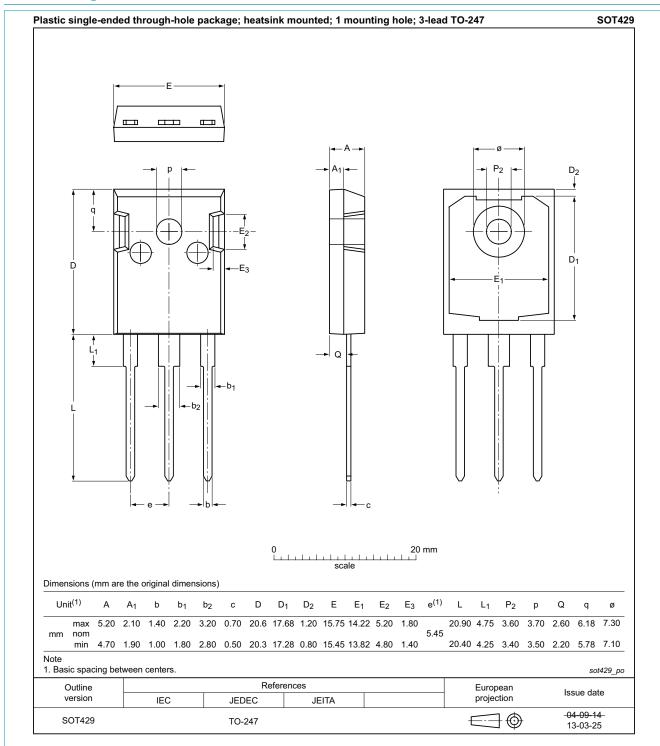


Fig. 7. Recovered charge as a function of junction temperature; per diode

## 11. Package outline



WNSC2D201200CW

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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